

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1-5. (Canceled)

6. (Currently Amended) A manufacturing method of a photo mask blank having at least a thin film for forming a pattern on a transparent substrate, said method comprising steps of:

setting a substrate in a horizontal position where a surface of the substrate on which said thin film is being formed and a surface of a sputtering [[a]] target are in [[an]] opposed positions with a center axis of said target deviating from a center axis of said substrate surface,

sputtering the target while rotating said substrate around its center axis so as to form said thin film.

7. (Original) The manufacturing method according to claim 6 wherein the target and the substrate are disposed so that opposite surfaces of said substrate and the target form a predetermined angle therebetween.

8. (Original) The manufacturing method according to claim 6 wherein the step of forming the film comprises a step of rotating the transparent substrate integer times between start of film formation and end of the film formation.

9. (Previously presented) The manufacturing method according to claim 7 wherein said thin

film for forming the pattern is a phase shift film, and said photo mask blank is a phase shift mask blank.

10. (Previously presented) The manufacturing method according to claim 8 wherein said thin film for forming the pattern is a phase shift film, and said photo mask blank is a phase shift mask blank.

11. (Canceled)

12. (Original) The manufacturing method according to claim 6 wherein said thin film for forming the pattern is a phase shift film, and said photo mask blank is a phase shift mask blank.

13. (Previously presented) The manufacturing method according to claim 12 wherein a dispersion of a phase angle of said phase shift film in a plane is within $\pm 2^\circ$.

14. (Original) The manufacturing method according to claim 6 wherein said thin film for forming the pattern is a light semi-transmission phase shift film, and said photo mask blank is a halftone phase shift mask blank.

15. (Original) The manufacturing method according to claim 14 wherein a dispersion of a phase angle of said light semi-transmission phase shift film in a plane is within $\pm 2^\circ$ and a dispersion of a transmittance in the plane is within $\pm 4\%$.

16. (Original) The manufacturing method according to claim 14 wherein said light semi-transmission phase shift film is formed by sputtering the target formed of a metal and silicon in an atmosphere containing nitrogen, contains the metal, silicon and nitrogen as main constituting components, and is formed so that a content of nitrogen in said light semi-transmission phase shift film is larger than a content of silicon.

17-25. (Canceled).